

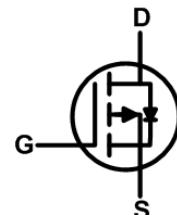
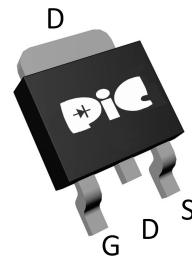
➤ General Description

This PAP01TX15X P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

➤ TO-252



➤ Application

- Switch application
- DC/DC Converters Power
- Tools

➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	-100	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current, V _{GS} @ -10V ¹	I _D @T _C =25°C	-18	A
Continuous Drain Current, V _{GS} @ -10V ¹	I _D @T _C =100°C	-12	A
Pulsed Drain Current ²	I _{DM}	-75	A
Single Pulse Avalanche Energy ³	EAS	157.2	mJ
Avalanche Current	I _{AS}	18.9	A
Total Power Dissipation ⁴	P _D @T _C =25°C	54	W
Storage Temperature Range	T _{STG}	-55 to 150	°C
Operating Junction Temperature Range	T _J	-55 to 150	°C
Thermal Resistance Junction-Ambient ¹	R _{θJA}	62	°C/W
Thermal Resistance Junction-Case ¹	R _{θJC}	2.3	°C/W

➤ **Electrical Characteristics (T_J=25°C Unless otherwise noted)**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V , I _D =-250uA	-100	---	---	V
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =-10V , I _D =-10A	---	78	95	mΩ
		V _{GS} =-4.5V , I _D =-8A	---	86	110	
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.7	-2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-100V , V _{GS} =0V , T _J =25°C	---	---	-50	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =-10V , I _D =-10A	---	24	---	S
Total Gate Charge	Q _g	V _{DS} =-50V , V _{GS} =-10V , I _D =-20A	---	44.5	---	nC
Gate-Source Charge	Q _{gs}		---	9.13	---	
Gate-Drain Charge	Q _{gd}		---	5.93	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =-50V , V _{GS} =-10V , R _G =3.3Ω, I _D =-10A	---	12	---	ns
Rise Time	T _r		---	27.4	---	
Turn-Off Delay Time	T _{d(off)}		---	79	---	
Fall Time	T _f		---	53.6	---	
Input Capacitance	C _{iss}	V _{DS} =-20V , V _{GS} =0V , f=1MHz	---	3029	---	pF
Output Capacitance	C _{oss}		---	129	---	
Reverse Transfer Capacitance	C _{rss}		---	76	---	

➤ **Diode Characteristics**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,5}	I _S	V _G =V _D =0V , Force Current	---	---	-18	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V , I _S =-1A , T _J =25°C	---	---	-1.2	V
Reverse Recovery Time	t _{rr}	I _F =-8A , di/dt=-100A/μs , T _J =25°C	---	38.7	---	nS
	Q _{rr}		---	22.4	---	nC

Note :

- 1.Pulse width limited by maximum junction temperature.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.88mH,I_{AS}=-18.9A
- 4.Ensure that the channel temperature does not exceed 150°C.
- 5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

➤ Typical Characteristics

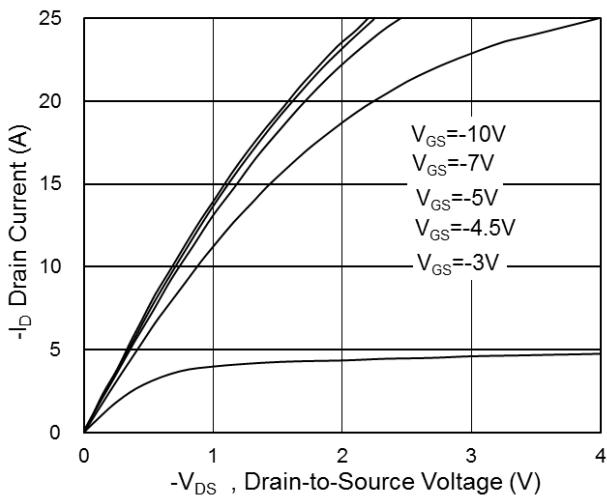


Fig.1 Typical Output Characteristics

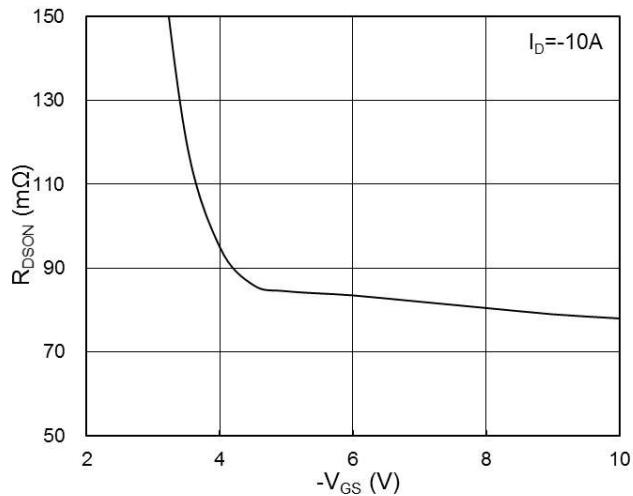


Fig.2 On-Resistance vs G-S Voltage

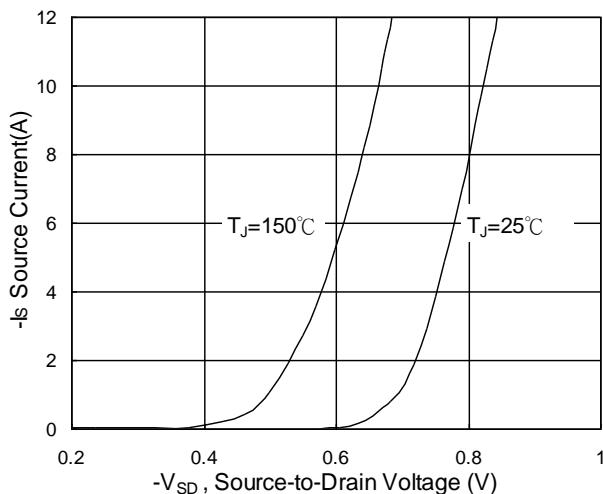


Fig.3 Typical S-D Diode Forward Voltage

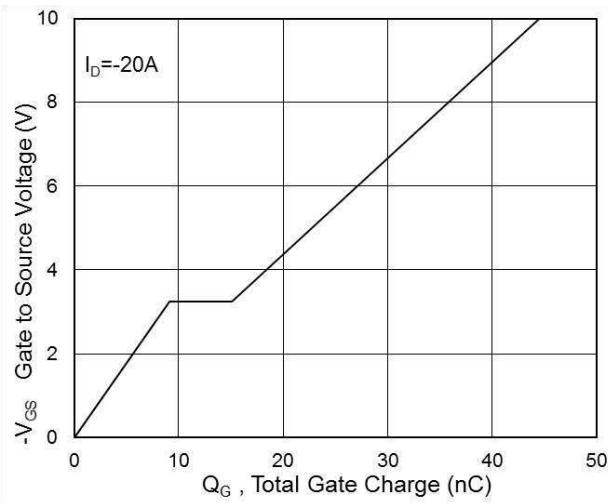


Fig.4 Gate-Charge Characteristics

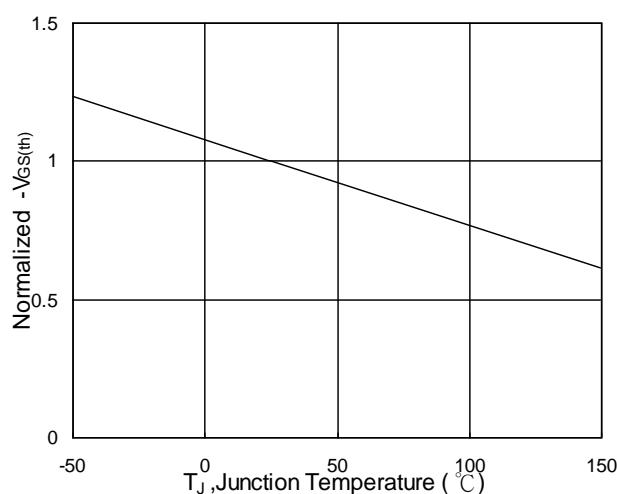


Fig.5 Normalized $V_{GS(\text{th})}$ vs T_J

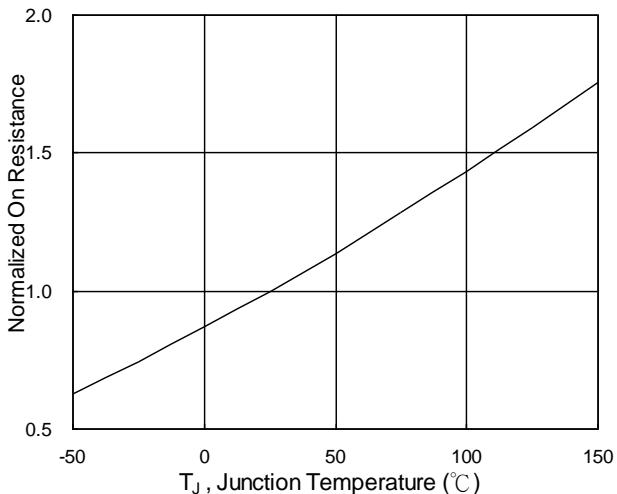
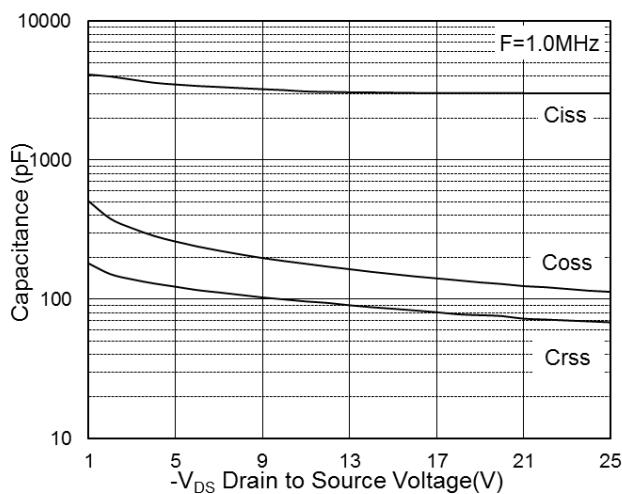
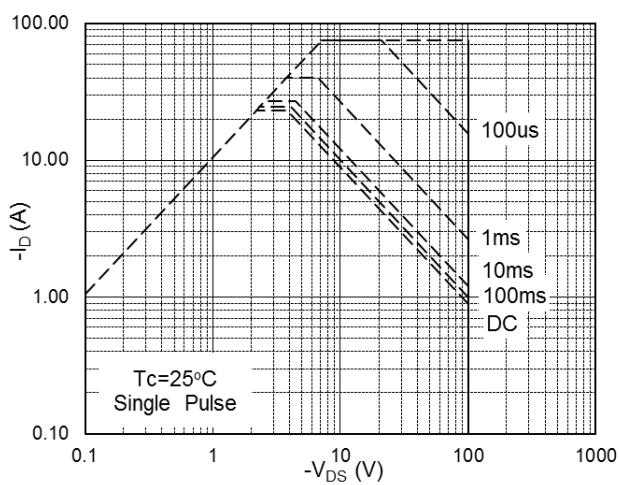
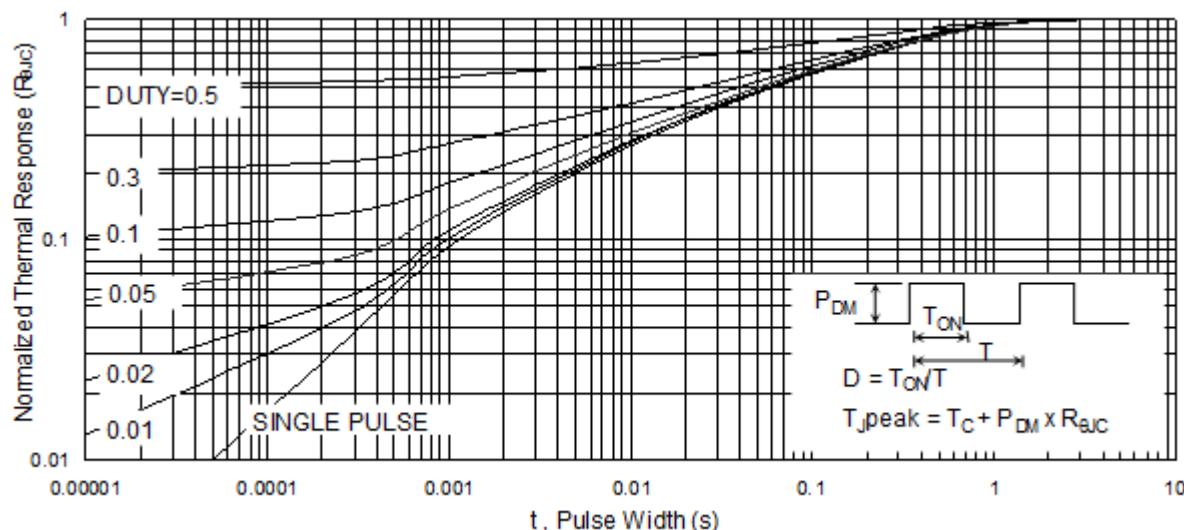
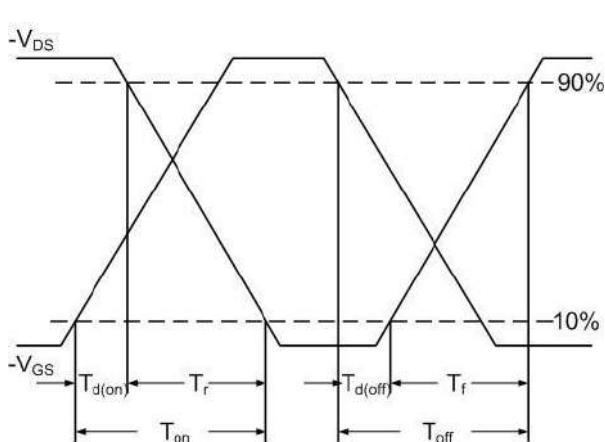
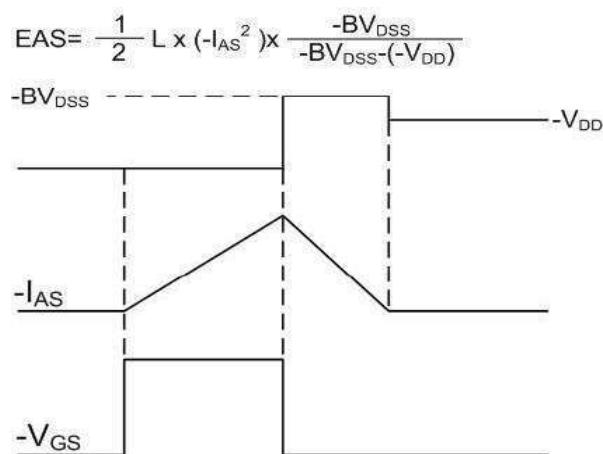
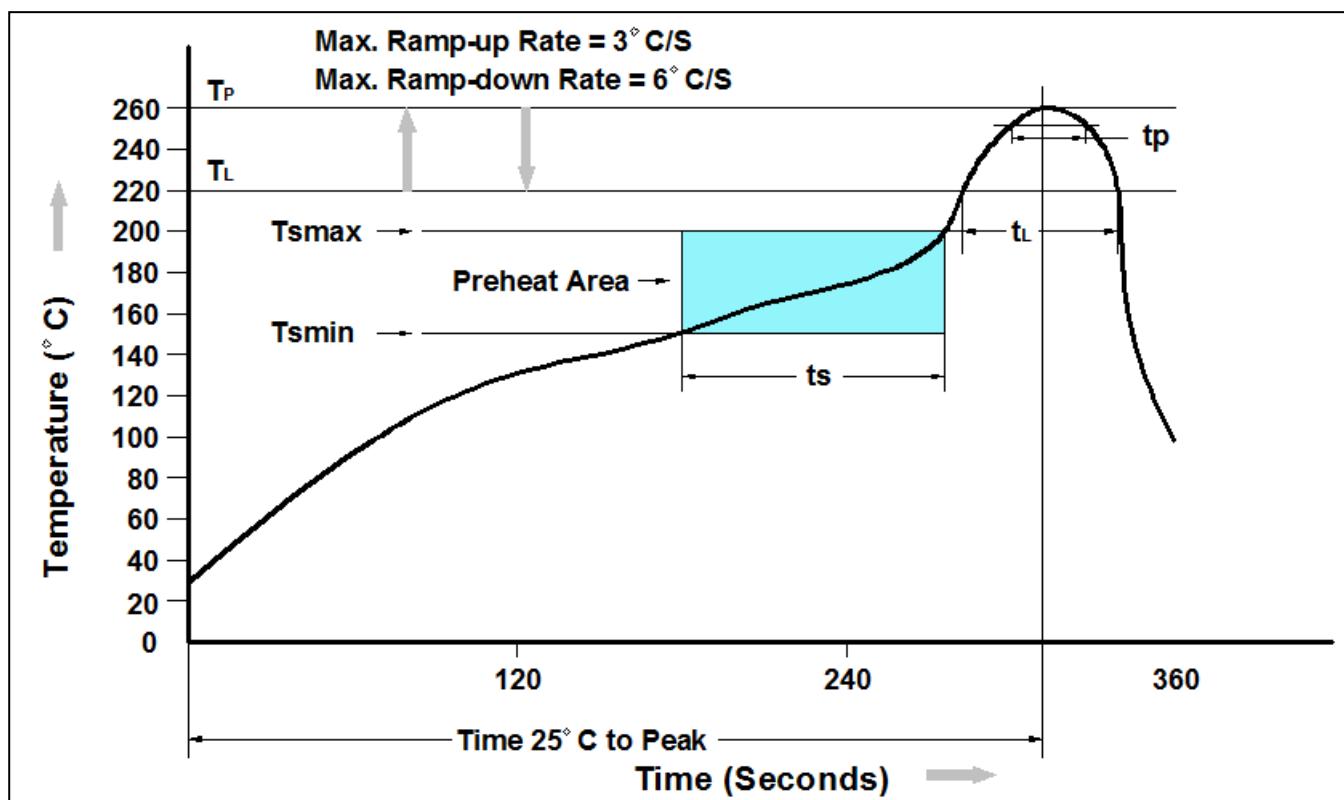


Fig.6 Normalized R_{DSON} vs T_J


Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Waveform

➤ Recommand IR Reflow Soldering Thermal Profile

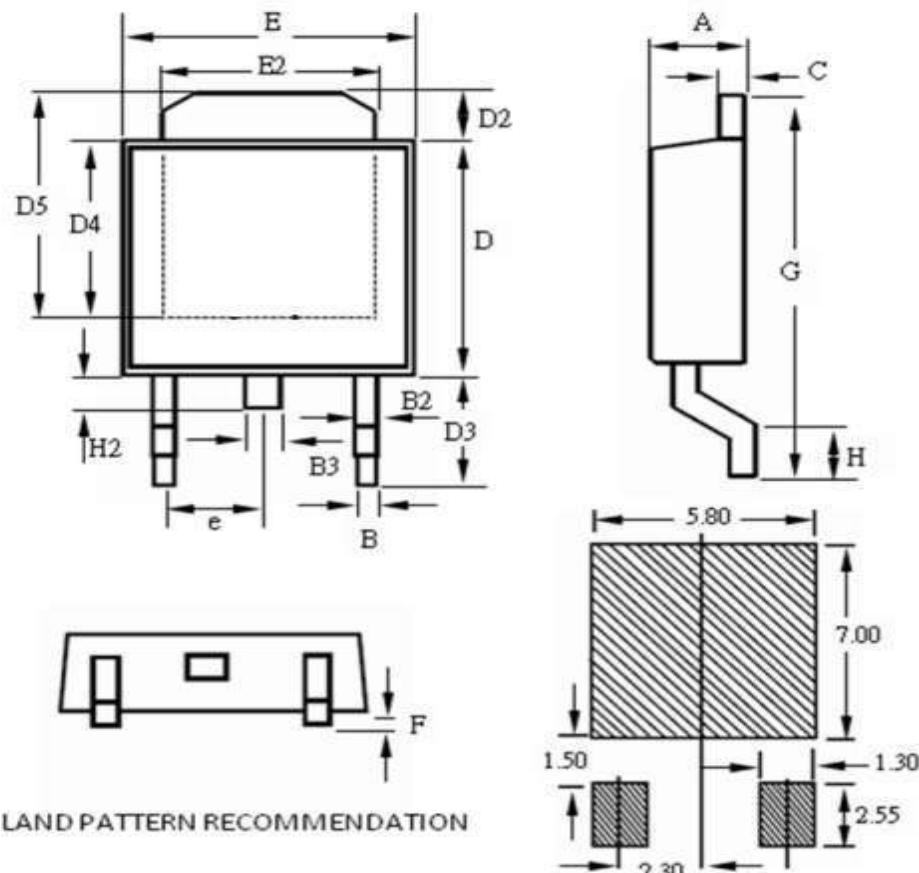


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Average Ramp-up Rate (tL to tp)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (tp) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAP01TX15X	TO-252 Reel	2500 pcs

➤ **Package Information (TO-252)**



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.10	--	2.50	0.083	--	0.098
B	0.30	--	0.89	0.012	--	0.035
B2	0.40	--	1.14	0.016	--	0.045
B3	0.60	--	1.00	0.024	--	0.039
C	0.40	--	0.89	0.016	--	0.035
D	5.30	--	6.25	0.209	--	0.246
D2	0.50	--	1.70	0.020	--	0.067
D3	2.20	--	3.40	0.087	--	0.134
D4	4.32	--	--	0.170	--	--
D5	5.21	--	--	0.205	--	--
E	6.30	--	6.73	0.248	--	0.265
E2	4.80	--	5.46	0.189	--	0.215
F	0.00	--	0.30	0.000	--	0.012
G	9.20	--	10.41	0.362	--	0.410
H	0.90	--	1.95	0.035	--	0.077
H2	0.50	--	1.10	0.020	--	0.043
e	--	2.30	--	--	0.091	--

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